

Hong-Long Ning

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

146
papers

2,000
citations

22
h-index

38
g-index

164
ext. papers

2,375
ext. citations

4.3
avg, IF

4.72
L-index

#	Paper	IF	Citations
146	High k PVP titanium dioxide composite dielectric with low leakage current for thin film transistor. <i>Organic Electronics</i> , 2022 , 101, 106413	3.5	2
145	Fabrication of flexible electrochromic film based on amorphous isopolytungstate by low-temperature inkjet-printed process with a solution crystallization kinetic-controlled strategy. <i>Chemical Engineering Journal</i> , 2022 , 427, 131840	14.7	1
144	Mini-LED Backlight Technology Progress for Liquid Crystal Display. <i>Crystals</i> , 2022 , 12, 313	2.3	1
143	Solution-Processed Silicon Doped Tin Oxide Thin Films and Thin-Film Transistors Based on Tetraethyl Orthosilicate. <i>Membranes</i> , 2022 , 12, 590	3.8	0
142	Research and Progress of Transparent, Flexible Tin Oxide Ultraviolet Photodetector. <i>Crystals</i> , 2021 , 11, 1479	2.3	0
141	Application of Laser Treatment in MOS-TFT Active Layer Prepared by Solution Method.. <i>Micromachines</i> , 2021 , 12,	3.3	1
140	Inkjet printing high performance flexible electrodes via a graphene decorated Ag ink. <i>Surfaces and Interfaces</i> , 2021 , 101609	4.1	1
139	Environmentally friendly, flexible and high performance PVA dielectric layer fabricated by solution method and its application in IGZO-TFT. <i>Organic Electronics</i> , 2021 , 100, 106383	3.5	1
138	Effect of laser energy on the properties of neodymium-doped indium zinc oxide thin films deposited by pulsed laser deposition. <i>Superlattices and Microstructures</i> , 2021 , 160, 107059	2.8	1
137	Alloy-Electrode-Assisted High-Performance Enhancement-Type Neodymium-Doped Indium-Zinc-Oxide Thin-Film Transistors on Polyimide Flexible Substrate. <i>Research</i> , 2021 , 2021, 5758435	7.8	3
136	Binary Solvent Systems for Piezoelectric Printing Crack-Free PAM/ZrO Hybrid Thin Films through Nanostructure Modulation. <i>Langmuir</i> , 2021 , 37, 5979-5985	4	0
135	High-Entropy Oxides: Advanced Research on Electrical Properties. <i>Coatings</i> , 2021 , 11, 628	2.9	9
134	The Investigation of Indium-Free Amorphous Zn-Al-Sn-O Thin Film Transistor Prepared by Magnetron Sputtering. <i>Coatings</i> , 2021 , 11, 585	2.9	0
133	Recent Developments in Flexible Transparent Electrode. <i>Crystals</i> , 2021 , 11, 511	2.3	8
132	Performances of thin film transistors with Ga-doped ZnO source and drain electrodes. <i>Journal Physics D: Applied Physics</i> , 2021 , 54, 365101	3	2
131	Bias Stress Stability of Solution-Processed Nano Indium Oxide Thin Film Transistor. <i>Micromachines</i> , 2021 , 12,	3.3	1
130	Temperature-Controlled Crystal Size of Wide Band Gap Nickel Oxide and Its Application in Electrochromism. <i>Micromachines</i> , 2021 , 12,	3.3	6

129	Study of the Correlation between the Amorphous Indium-Gallium-Zinc Oxide Film Quality and the Thin-Film Transistor Performance. <i>Nanomaterials</i> , 2021 , 11,	5.4	1
128	Implementing Room-Temperature Fabrication of Flexible Amorphous SnBiO ₂ TFTs via Defect Control. <i>Advanced Materials Interfaces</i> , 2021 , 8, 2002193	4.6	0
127	Modifying Precursor Solutions to Obtain Screen-Printable Inks for Tungsten Oxides Electrochromic Film Preparation. <i>Coatings</i> , 2021 , 11, 872	2.9	1
126	48.1: Invited Paper: Inkjet printing of homogeneous and green cellulose nanofibrils dielectric for high performance IGZO TFTs. <i>Digest of Technical Papers SID International Symposium</i> , 2021 , 52, 580-581	0.5	
125	48.3: Ag Ink Patterning and Application Using Electrohydrodynamic Jet Printing. <i>Digest of Technical Papers SID International Symposium</i> , 2021 , 52, 586-587	0.5	
124	Highly conductive and adhesive ternary CuCrZr alloy electrode for flexible optoelectronic applications. <i>Superlattices and Microstructures</i> , 2021 , 157, 106989	2.8	2
123	Zirconium-aluminum co-doping on solution-processed indium oxide thin film and deceives measured by a novel nondestructive method. <i>Surfaces and Interfaces</i> , 2021 , 27, 101459	4.1	1
122	Physical Simulation Model of WO Electrochromic Films Based on Continuous Electron-Transfer Kinetics and Experimental Verification. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 4768-4776	9.5	7
121	Zirconium-Aluminum-Oxide Dielectric Layer with High Dielectric and Relatively Low Leakage Prepared by Spin-Coating and the Application in Thin-Film Transistor. <i>Coatings</i> , 2020 , 10, 282	2.9	8
120	Effect of the Ammonium Tungsten Precursor Solution with the Modification of Glycerol on Wide Band Gap WO Thin Film and Its Electrochromic Properties. <i>Micromachines</i> , 2020 , 11,	3.3	6
119	Origin of bias-stress and illumination instability in low-cost, wide-bandgap amorphous Si-doped tin oxide-based thin-film transistors. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 235102	3	2
118	Oxygen incorporated solution-processed high- κ La ₂ O ₃ dielectrics with large-area uniformity, low leakage and high breakdown field comparable with ALD deposited films. <i>Journal of Materials Chemistry C</i> , 2020 , 8, 5163-5173	7.1	5
117	High-Performance and Flexible Neodymium-Doped Indium-Zinc-Oxide Thin-Film Transistor With All Copper Alloy Electrodes. <i>IEEE Electron Device Letters</i> , 2020 , 41, 417-420	4.4	4
116	Sol-gel synthesis of large-sized polycrystalline stannous oxide and its oxidation behavior. <i>CrystEngComm</i> , 2020 , 22, 1834-1838	3.3	0
115	Preparation and optimization of SnOx thin film by solution method at low temperature. <i>Superlattices and Microstructures</i> , 2020 , 139, 106400	2.8	4
114	Effects of rapid thermal annealing on wide band gap tungsten oxide films. <i>Superlattices and Microstructures</i> , 2020 , 142, 106541	2.8	2
113	Preparation of Highly Transparent (at 450-800 nm) SnO ₂ Homo Junction by Solution Method and Its Photoresponse. <i>Coatings</i> , 2020 , 10, 399	2.9	4
112	Effect of deep UV laser treatment on silicon-doped Tin oxide thin film. <i>Journal of the Society for Information Display</i> , 2020 , 28, 194-203	2.1	1

111	Fabrication of high-performance solution processed thin film transistors by introducing a buffer layer. <i>Applied Surface Science</i> , 2020 , 504, 144360	6.7	5
110	Effect of oxygen pressure on GZO film as active layer of the TFT fabricated at room temperature. <i>Superlattices and Microstructures</i> , 2020 , 137, 106317	2.8	5
109	Highly Efficient Metal-Free Two-Dimensional Luminescent Melem Nanosheets for Bioimaging. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 2145-2151	9.5	14
108	Effect of Zirconium Doping on Electrical Properties of Aluminum Oxide Dielectric Layer by Spin Coating Method with Low Temperature Preparation. <i>Coatings</i> , 2020 , 10, 620	2.9	3
107	Functional Metal Oxide Ink Systems for Drop-on-Demand Printed Thin-Film Transistors. <i>Langmuir</i> , 2020 , 36, 8655-8667	4	7
106	Study of Inkjet-Printed Silver Films Based on Nanoparticles and Metal-Organic Decomposition Inks with Different Curing Methods. <i>Micromachines</i> , 2020 , 11,	3.3	6
105	Inkjet printing of homogeneous and green cellulose nanofibril dielectrics for high performance IGZO TFTs. <i>Journal of Materials Chemistry C</i> , 2020 , 8, 12578-12586	7.1	4
104	Research Progress of High Dielectric Constant Zirconia-Based Materials for Gate Dielectric Application. <i>Coatings</i> , 2020 , 10, 698	2.9	8
103	Investigation of direct inkjet-printed versus spin-coated ZrO for sputter IGZO thin film transistor. <i>Nanoscale Research Letters</i> , 2019 , 14, 80	5	7
102	All-Sputtering, High-Transparency, Good-Stability Coplanar Top-Gate Thin Film Transistors. <i>Applied Sciences (Switzerland)</i> , 2019 , 9, 83	2.6	3
101	Polymer-Doped Ink System for Threshold Voltage Modulation in Printed Metal Oxide Thin Film Transistors. <i>Journal of Physical Chemistry Letters</i> , 2019 , 10, 3415-3419	6.4	5
100	Tungsten doped stannic oxide transparent conductive thin film using preoxotungstic acid dopant. <i>Superlattices and Microstructures</i> , 2019 , 130, 277-284	2.8	3
99	Evaluation of Nd/Al doped indium-zinc oxide thin-film transistors by a EPCD method. <i>Semiconductor Science and Technology</i> , 2019 , 34, 055011	1.8	3
98	Evaporation induced hollow cracks and the adhesion of silver nanoparticle film. <i>Journal of Materials Science</i> , 2019 , 54, 7987-7996	4.3	3
97	Room-Temperature Fabrication of High-Quality Lanthanum Oxide High- κ Dielectric Films by a Solution Process for Low-Power Soft Electronics. <i>Advanced Electronic Materials</i> , 2019 , 5, 1900427	6.4	6
96	Effects of praseodymium doping on the electrical properties and aging effect of InZnO thin-film transistor. <i>Journal of Materials Science</i> , 2019 , 54, 14778-14786	4.3	12
95	The Effect of Zirconium Doping on Solution-Processed Indium Oxide Thin Films Measured by a Novel Nondestructive Testing Method (Microwave Photoconductivity Decay). <i>Coatings</i> , 2019 , 9, 426	2.9	3
94	A Strategy toward Realizing Ultrashort Channels and Microstructures Array by Piezoelectric Inkjet Printing. <i>Nanomaterials</i> , 2019 , 9,	5.4	1

93	The Performance of Zr-Doped Al-Zn-Sn-O Thin Film Transistor Prepared by Co-Sputtering. <i>Applied Sciences (Switzerland)</i> , 2019 , 9, 5150	2.6	4
92	Effective Evaluation Strategy Toward Low Temperature Solution-Processed Oxide Dielectrics for TFT Device. <i>IEEE Journal of the Electron Devices Society</i> , 2019 , 7, 1140-1144	2.3	1
91	34.4: Invited Paper: Inkjet printed high-performance ZrO ₂ dielectric for TFT device. <i>Digest of Technical Papers SID International Symposium</i> , 2019 , 50, 379-380	0.5	
90	Flexible thin-film transistors application of amorphous tin oxide-based semiconductors. <i>Journal of the Society for Information Display</i> , 2019 , 27, 769-775	2.1	3
89	Density functional theory study of the electronic and optical properties of Si incorporated SnO ₂ . <i>AIP Advances</i> , 2019 , 9, 115104	1.5	2
88	Thermal effect of annealing-temperature on solution-processed high- ZrO dielectrics.. <i>RSC Advances</i> , 2019 , 9, 42415-42422	3.7	5
87	A Simple, Low Cost Ink System for Drop-on-Demand Printing High Performance Metal Oxide Dielectric Film at Low Temperature. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 5193-5199	9.5	9
86	Trap-Assisted Enhanced Bias Illumination Stability of Oxide Thin Film Transistor by Praseodymium Doping. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 5232-5239	9.5	20
85	Gel-Switchable Droplet Front for Large-Scale Uniformity of Inkjet Printed Silver Patterns. <i>Advanced Materials Technologies</i> , 2019 , 4, 1800243	6.8	5
84	Solution processable high quality ZrO ₂ dielectric films for low operation voltage and flexible organic thin film transistor applications. <i>Journal Physics D: Applied Physics</i> , 2018 , 51, 115105	3	15
83	Room Temperature Fabrication of High Quality ZrO ₂ Dielectric Films for High Performance Flexible Organic Transistor Applications. <i>IEEE Electron Device Letters</i> , 2018 , 39, 280-283	4.4	12
82	Effect of ITO Serving as a Barrier Layer for Cu Electrodes on Performance of a-IGZO TFT. <i>IEEE Electron Device Letters</i> , 2018 , 39, 504-507	4.4	18
81	High-performance flexible oxide TFTs: optimization of a-IGZO film by modulating the voltage waveform of pulse DC magnetron sputtering without post treatment. <i>Journal of Materials Chemistry C</i> , 2018 , 6, 2522-2532	7.1	24
80	High conductivity and transparent aluminum-based multi-layer source/drain electrodes for thin film transistors. <i>Journal Physics D: Applied Physics</i> , 2018 , 51, 065103	3	3
79	High-Performance and Flexible Neodymium- Doped Oxide Semiconductor Thin-Film Transistors With Copper Alloy Bottom-Gate Electrode. <i>IEEE Electron Device Letters</i> , 2018 , 39, 839-842	4.4	7
78	Reduced contact resistance of a-IGZO thin film transistors with inkjet-printed silver electrodes. <i>Journal Physics D: Applied Physics</i> , 2018 , 51, 165103	3	9
77	Effect of Al ₂ O ₃ Passivation Layer and Cu Electrodes on High Mobility of Amorphous IZO TFT. <i>IEEE Journal of the Electron Devices Society</i> , 2018 , 6, 733-737	2.3	16
76	Induced nano-scale self-formed metal-oxide interlayer in amorphous silicon tin oxide thin film transistors. <i>Scientific Reports</i> , 2018 , 8, 4160	4.9	3

75	Facile Room Temperature Routes to Improve Performance of IGZO Thin-Film Transistors by an Ultrathin Al ₂ O ₃ Passivation Layer. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 537-541	2.9	8
74	Low-temperature fabrication of sputtered high-k HfO ₂ gate dielectric for flexible a-IGZO thin film transistors. <i>Applied Physics Letters</i> , 2018 , 112, 103503	3.4	66
73	Inkjet Printed Electrodes in Thin Film Transistors. <i>IEEE Journal of the Electron Devices Society</i> , 2018 , 6, 774-790	2.3	15
72	Effects of Annealing Temperature on Optical Band Gap of Sol-gel Tungsten Trioxide Films. <i>Micromachines</i> , 2018 , 9,	3.3	25
71	Efficient Bipolar Blue AIEgens for High-Performance Nondoped Blue OLEDs and Hybrid White OLEDs. <i>Advanced Functional Materials</i> , 2018 , 28, 1803369	15.6	103
70	Mobility Enhancement in Amorphous In-Ga-Zn-O Thin-Film Transistor by Induced Metallic in Nanoparticles and Cu Electrodes. <i>Nanomaterials</i> , 2018 , 8,	5.4	16
69	High-performance spin-coated aluminum oxide dielectric fabricated by a simple oxygen plasma-treatment process. <i>Journal Physics D: Applied Physics</i> , 2018 , 51, 365101	3	9
68	Bias Stability Enhancement in Thin-Film Transistor with a Solution-Processed ZrO ₂ Dielectric as Gate Insulator. <i>Applied Sciences (Switzerland)</i> , 2018 , 8, 806	2.6	5
67	Enhanced Transmittance Modulation of SiO ₂ -Doped Crystalline WO ₃ Films Prepared from a Polyethylene Oxide (PEO) Template. <i>Coatings</i> , 2018 , 8, 228	2.9	7
66	A Semi-Analytical Extraction Method for Interface and Bulk Density of States in Metal Oxide Thin-Film Transistors. <i>Materials</i> , 2018 , 11,	3.5	1
65	Effect of Source/Drain Electrodes on the Electrical Properties of Silicon?Tin Oxide Thin-Film Transistors. <i>Nanomaterials</i> , 2018 , 8,	5.4	6
64	Lattice defects of ZnO and hybrids with GO: Characterization, EPR and optoelectronic properties. <i>AIP Advances</i> , 2018 , 8, 025218	1.5	21
63	Protonation Process to Enhance the Water Resistance of Transparent and Hazy Paper. <i>ACS Sustainable Chemistry and Engineering</i> , 2018 , 6, 12385-12392	8.3	15
62	48.2: Invited Paper: High conductivity & transparent aluminum-based multi-layer source/drain electrodes for thin film transistors. <i>Digest of Technical Papers SID International Symposium</i> , 2018 , 49, 504-508	0.5	
61	35.3: Self-formed nano-scale metal-oxide contact interlayer for amorphous silicon tin oxide TFTs. <i>Digest of Technical Papers SID International Symposium</i> , 2018 , 49, 385-394	0.5	
60	Inkjet printing satellite-free silver electrodes array in a-IGZO TFTs by regulating piezoelectric waveforms. <i>Molecular Crystals and Liquid Crystals</i> , 2018 , 676, 36-43	0.5	0
59	The effect of different annealing temperature on transparent conductive SnO ₂ thin film by solution process. <i>Molecular Crystals and Liquid Crystals</i> , 2018 , 676, 44-49	0.5	2
58	Zigzag Hollow Cracks of Silver Nanoparticle Film Regulated by Its Drying Micro-environment. <i>Nanoscale Research Letters</i> , 2018 , 13, 354	5	1

57	Highly Conductive and Transparent AZO Films Fabricated by PLD as Source/Drain Electrodes for TFTs. <i>Materials</i> , 2018 , 11,	3.5	4
56	P-6.10: LTPS-TFT Process for OLED and some issues generated from the manufacturing. <i>Digest of Technical Papers SID International Symposium</i> , 2018 , 49, 625-631	0.5	4
55	Capillary force induced air film for self-aligned short channel: pushing the limits of inkjet printing. <i>Soft Matter</i> , 2018 , 14, 9402-9410	3.6	4
54	A study of contact properties between molybdenum and amorphous silicon tin oxide thin film transistors. <i>Journal of the Society for Information Display</i> , 2018 , 26, 681-686	2.1	2
53	High-Performance Thin Film Transistor with an Neodymium-Doped Indium Zinc Oxide/Al ₂ O ₃ Nanolaminate Structure Processed at Room Temperature. <i>Materials</i> , 2018 , 11,	3.5	2
52	Characterization studies of the structure and properties of Zr-doped SnO ₂ thin films by spin-coating technique. <i>Superlattices and Microstructures</i> , 2018 , 123, 330-337	2.8	19
51	Enhancement of Electrical Characteristics and Stability of Amorphous Si-Sn-O Thin Film Transistors with SiO Passivation Layer. <i>Materials</i> , 2018 , 11,	3.5	8
50	Morphology Modulation of Direct Inkjet Printing by Incorporating Polymers and Surfactants into a Sol-Gel Ink System. <i>Langmuir</i> , 2018 , 34, 6413-6419	4	20
49	Critical Impact of Solvent Evaporation on the Resolution of Inkjet Printed Nanoparticles Film. <i>ACS Applied Materials & Interfaces</i> , 2018 , 10, 22883-22888	9.5	8
48	Programmable Shape Recovery Process of Water-Responsive Shape-Memory Poly(vinyl alcohol) by Wettability Contrast Strategy. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 5495-5502	9.5	40
47	Homogeneous Surface Profiles of Inkjet-Printed Silver Nanoparticle Films by Regulating Their Drying Microenvironment. <i>Journal of Physical Chemistry C</i> , 2017 , 121, 8992-8998	3.8	13
46	A room temperature strategy towards enhanced performance and bias stability of oxide thin film transistor with a sandwich structure channel layer. <i>Applied Physics Letters</i> , 2017 , 110, 153503	3.4	9
45	All-sputtered, flexible, bottom-gate IGZO/Al ₂ O ₃ bi-layer thin film transistors on PEN fabricated by a fully room temperature process. <i>Journal of Materials Chemistry C</i> , 2017 , 5, 7043-7050	7.1	43
44	Island-Like AZO/Al ₂ O ₃ Bilayer Channel Structure for Thin Film Transistors. <i>Advanced Materials Interfaces</i> , 2017 , 4, 1700063	4.6	6
43	High Mobility Amorphous Indium-Gallium-Zinc-Oxide Thin-Film Transistor by Aluminum Oxide Passivation Layer. <i>IEEE Electron Device Letters</i> , 2017 , 38, 879-882	4.4	38
42	Highly conductive AZO thin films obtained by rationally optimizing substrate temperature and oxygen partial pressure. <i>Molecular Crystals and Liquid Crystals</i> , 2017 , 644, 190-196	0.5	2
41	Stable ambipolar organic/organic heterojunction field-effect transistors and inverters with Cytop interlayer. <i>RSC Advances</i> , 2017 , 7, 5966-5969	3.7	11
40	UV-Cured Inkjet-Printed Silver Gate Electrode with Low Electrical Resistivity. <i>Nanoscale Research Letters</i> , 2017 , 12, 546	5	5

39	Properties-Adjustable Alumina-Zirconia Nanolaminate Dielectric Fabricated by Spin-Coating. <i>Nanomaterials</i> , 2017 , 7,	5.4	4
38	Doping-free tandem white organic light-emitting diodes. <i>Science Bulletin</i> , 2017 , 62, 1193-1200	10.6	28
37	High-Performance Doping-Free Hybrid White OLEDs Based on Blue Aggregation-Induced Emission Luminogens. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 34162-34171	9.5	59
36	Room-Temperature Fabrication of High-Performance Amorphous In-Ga-Zn-O/AlO ₃ Thin-Film Transistors on Ultrasoother and Clear Nanopaper. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 27792-27800 ³²	9.5	32
35	Highly Transparent and Self-Extinguishing Nanofibrillated Cellulose-Monolayer Clay Nanoplatelet Hybrid Films. <i>Langmuir</i> , 2017 , 33, 8455-8462	4	19
34	Direct patterning of silver electrodes with 2.4 μ m channel length by piezoelectric inkjet printing. <i>Journal of Colloid and Interface Science</i> , 2017 , 487, 68-72	9.3	22
33	Effect of Intrinsic Stress on Structural and Optical Properties of Amorphous Si-Doped SnO ₂ Thin-Film. <i>Materials</i> , 2017 , 10,	3.5	10
32	Direct Inkjet Printing of Silver Source/Drain Electrodes on an Amorphous InGaZnO Layer for Thin-Film Transistors. <i>Materials</i> , 2017 , 10,	3.5	20
31	All-Aluminum Thin Film Transistor Fabrication at Room Temperature. <i>Materials</i> , 2017 , 10,	3.5	11
30	A Simple Method for High-Performance, Solution-Processed, Amorphous ZrO ₂ Gate Insulator TFT with a High Concentration Precursor. <i>Materials</i> , 2017 , 10,	3.5	19
29	High Conductivity and Adhesion of Cu-Cr-Zr Alloy for TFT Gate Electrode. <i>Applied Sciences (Switzerland)</i> , 2017 , 7, 820	2.6	6
28	Amorphous InGaZnO Thin Film Transistor Fabricated with Printed Silver Salt Ink Source/Drain Electrodes. <i>Applied Sciences (Switzerland)</i> , 2017 , 7, 844	2.6	8
27	A Low-Power High-Stability Flexible Scan Driver Integrated by IZO TFTs. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 1779-1782	2.9	20
26	Effect of Post Treatment For Cu-Cr Source/Drain Electrodes on a-IGZO TFTs. <i>Materials</i> , 2016 , 9,	3.5	17
25	Manipulation of Charge and Exciton Distribution Based on Blue Aggregation-Induced Emission Fluorophors: A Novel Concept to Achieve High-Performance Hybrid White Organic Light-Emitting Diodes. <i>Advanced Functional Materials</i> , 2016 , 26, 776-783	15.6	171
24	High-performance back-channel-etched thin-film transistors with amorphous Si-incorporated SnO ₂ active layer. <i>Applied Physics Letters</i> , 2016 , 108, 112106	3.4	22
23	A novel nondestructive testing method for amorphous Si ₃ N ₄ films. <i>Journal Physics D: Applied Physics</i> , 2016 , 49, 505102	3	14
22	High-performance doping-free hybrid white organic light-emitting diodes: The exploitation of ultrathin emitting nanolayers (. <i>Nano Energy</i> , 2016 , 26, 26-36	17.1	84

21	Extremely high-efficiency and ultrasimplified hybrid white organic light-emitting diodes exploiting double multifunctional blue emitting layers. <i>Light: Science and Applications</i> , 2016 , 5, e16137	16.7	94
20	Effects of Rare-Earth Element Dopants in High-Mobility InOx-Based Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2016 , 37, 1139-1142	4.4	7
19	Harnessing charge and exciton distribution towards extremely high performance: the critical role of guests in single-emitting-layer white OLEDs. <i>Materials Horizons</i> , 2015 , 2, 536-544	14.4	44
18	. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 2226-2230	2.9	11
17	A host-guest system comprising high guest concentration to achieve simplified and high-performance hybrid white organic light-emitting diodes. <i>Journal of Materials Chemistry C</i> , 2015 , 3, 6359-6366	7.1	36
16	High-performance hybrid white organic light-emitting diodes employing p-type interlayers. <i>Journal of Industrial and Engineering Chemistry</i> , 2015 , 27, 240-244	6.3	17
15	Method for Fabricating Amorphous Indium-Zinc-Oxide Thin-Film Transistors With Copper Source and Drain Electrodes. <i>IEEE Electron Device Letters</i> , 2015 , 36, 342-344	4.4	21
14	An ideal host-guest system to accomplish high-performance greenish yellow and hybrid white organic light-emitting diodes. <i>Organic Electronics</i> , 2015 , 27, 29-34	3.5	23
13	High-mobility thin film transistors with neodymium-substituted indium oxide active layer. <i>Applied Physics Letters</i> , 2015 , 107, 112108	3.4	26
12	Letter: A new compensation pixel circuit with metal oxide thin-film transistors for active-matrix organic light-emitting diode displays. <i>Journal of the Society for Information Display</i> , 2015 , 23, 233-239	2.1	3
11	Solution-processed indium-zinc-oxide thin-film transistors based on anodized aluminum oxide gate insulator modified with zirconium oxide. <i>RSC Advances</i> , 2015 , 5, 51440-51445	3.7	17
10	Efficient single-emitting layer hybrid white organic light-emitting diodes with low efficiency roll-off, stable color and extremely high luminance. <i>Journal of Industrial and Engineering Chemistry</i> , 2015 , 30, 85-91	6.3	19
9	Efficient hybrid white organic light-emitting diodes with extremely long lifetime: the effect of n-type interlayer. <i>Scientific Reports</i> , 2014 , 4, 7198	4.9	39
8	Extremely stable-color flexible white organic light-emitting diodes with efficiency exceeding 100 lm W ⁻¹ . <i>Journal of Materials Chemistry C</i> , 2014 , 2, 9836-9841	7.1	44
7	Regulating charges and excitons in simplified hybrid white organic light-emitting diodes: The key role of concentration in single dopant host-guest systems. <i>Organic Electronics</i> , 2014 , 15, 2616-2623	3.5	30
6	Effects of Solvent Treatment on the Characteristics of InGaZnO Thin-Film Transistors. <i>ECS Journal of Solid State Science and Technology</i> , 2014 , 3, Q3081-Q3084	2	8
5	INVESTIGATION OF THE INTERFACE OF THE DCB SUBSTRATE. <i>Surface Review and Letters</i> , 2003 , 10, 95-99.	0.1	0
4	Joining of sapphire and hot pressed Al ₂ O ₃ using Ag _{70.5} Cu _{27.5} Ti ₂ brazing filler metal. <i>Ceramics International</i> , 2003 , 29, 689-694	5.1	35

- 3 Preoxidation of the Cu layer in direct bonding technology. *Applied Surface Science*, **2003**, 211, 250-258 6.7 18
- 2 Precipitation in CuNiSiZn alloy for lead frame. *Materials Letters*, **2003**, 57, 2135-2139 3.3 60
- 1 Thermo-oxidative stability of SnO crystals and obtained few layer crystals by mechanical exfoliation. *Molecular Crystals and Liquid Crystals*, 1-7 0.5